

N-Ch MOSFET

General Description

The WST2088A is the highest performance trench N-ch MOSFETs with extreme high cell density , which provide excellent RDSON and gate charge for most of the small power switching and load switch applications.

The WST2088A meet the RoHS and Green Product requirement with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Green Device Available

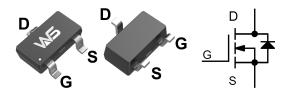
Product Summery

BVDSS	RDSON	ID
20V	10.7mΩ	7.5A

Applications

- Power switching application
- Hard Switched and High Frequency Circuits
- Uninterruptible Power Supply

SOT-23-3L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units	
V_{DS}	Drain-Source Voltage	20	V	
V_{GS}	Gate-Source Voltage	±12	V	
I _D @T _c =25℃	Continuous Drain Current, V _{GS} @ 4.5V	7.5	Α	
I _D @T _c =70℃	Continuous Drain Current, V _{GS} @ 4.5V	4.5	А	
I _{DP}	Pulsed Drain Current	24	Α	
P _D @T _A =25°C	Total Power Dissipation	1.25	W	
T _{STG}	Storage Temperature Range	-55 to 150	$^{\circ}$	
TJ	Operating Junction Temperature Range -55 to 150		$^{\circ}$	

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit
Rthj-a	Maximum Thermal Resistance, Junction-ambient		100	°C/W
Rthj-c	Maximum Thermal Resistance, Junction-case		8	°C/W



Electrical Characteristics (T_J=25 C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	20			V
$\triangle BV_{DSS}/\triangle T_{J}$	BVDSS Temperature Coefficient	Reference to 25℃, I _D =1mA		0.018		V/°C
Б	Static Dunin Source On Desistance ²	V _{GS} =4.5V , I _D =6A		10.7	14	0
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =2.5V , I _D =5A		12.8	17	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250uA$	0.4	0.63	1.2	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =16V , V _{GS} =0V.			10	uA
I _{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 12V$, V_{DS} =0V			±100	nA
Qg	Total Gate Charge			10		
Q_{gs}	Gate-Source Charge	V _{DS} =15V , V _{GS} =4.5V , I _D =6A		1.6		nC
Q_{gd}	Gate-Drain Charge			3.4		
$T_{d(on)}$	Turn-On Delay Time			8		
Tr	Rise Time	V _{DS} =10V , V _{GS} =4.5V ,		15		ne
T _{d(off)}	Turn-Off Delay Time	$R_G=3.3\Omega I_D=1A$		33		ns
T _f	Fall Time			13		
C _{iss}	Input Capacitance			590		
Coss	Output Capacitance	V _{DS} =15V , V _{GS} =0V , f=1MHz		125		pF
C _{rss}	Reverse Transfer Capacitance			90		

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
V _{SD}	Diode Forward Voltage	V _{GS} =0V , I _S =1A			1.2	V
t _{rr}	Reverse Recovery Time	IF=1A , V _{GS} =0V,				nS
Qrr	Reverse Recovery Charge	dl/dt=100A/µs				nC

A: The value of R e JA is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with TA=25°C. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The current rating is based on the t≤ 10s junction to ambient thermal resistance rating.



Typical Characteristics

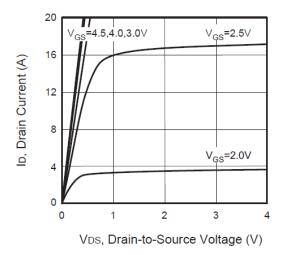


Figure 1. Output Characteristics

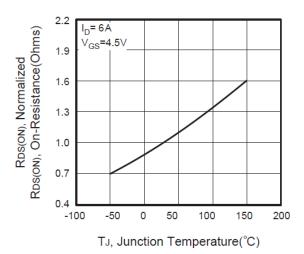


Figure 3. On-Resistance Variation with Temperature

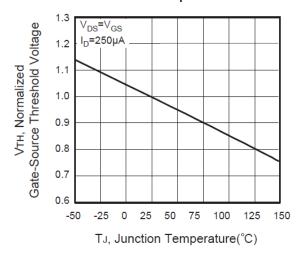


Figure 5. Gate Threshold Variation with Temperature

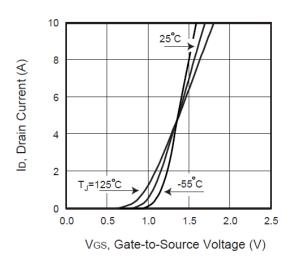


Figure 2. Transfer Characteristics

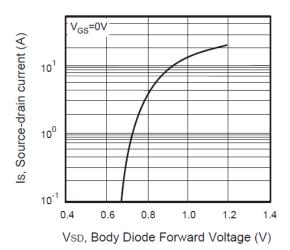


Figure 4. Body Diode Forward Voltage Variation with Source Current

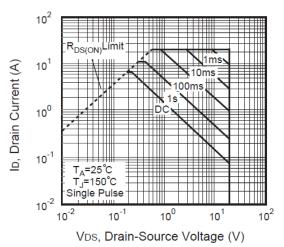
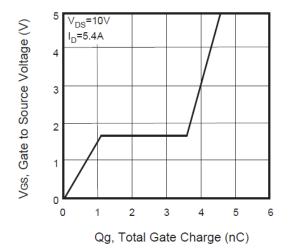


Figure 6. Maximum Safe Operating Area





td(on) tr td(off) tr td(off) yow to your 10% INVERTED 10%

VIN 10% FULSE WIDTH

Figure 7. Gate Charge

VGS RGEN G S S

Figure 8. Switching Waveforms

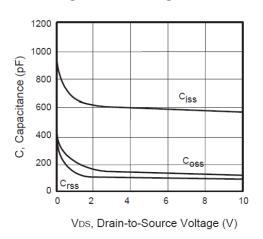


Figure 10.Capacitance

Figure 9. Switching Test Circuit

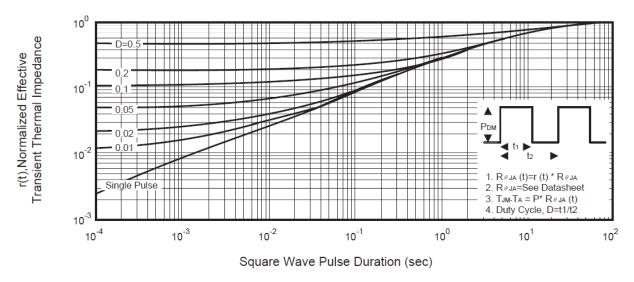


Figure 11. Normalized Thermal Transient Impedance Curve



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EFC2J004NUZTDG FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE2384 NTE2969 NTE6400A DMC2700UDMQ-7
DMN2080UCB4-7 DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7 SSM6P54TU,LF DMP22D4UFO-7B IPS60R3K4CEAKMA1 DMN1006UCA6-7 DMN16M9UCA6-7 STF5N65M6 IRF40H233XTMA1 IPSA70R950CEAKMA1 IPSA70R2K0CEAKMA1 STU5N65M6 C3M0021120D